

BCR8PM-20

MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

BCR8PM-20

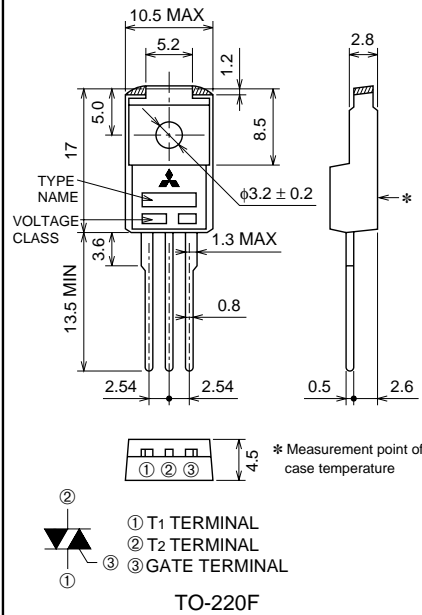


- IT (RMS) 8A
- VDRM 1000V
- IFGT I , IRGT I , IRGT III 30mA
- Viso 2000V
- UL Recognized: Yellow Card No.E80276(N)

File No. E80271

OUTLINE DRAWING

Dimensions
in mm



APPLICATION

Switching mode power supply, light dimmer, electric flasher unit,
control of household equipment such as TV sets · stereo · refrigerator · washing machine · infrared
kotatsu · carpet, solenoid drivers, small motor control,
copying machine, electric tool,
other general purpose control applications

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
		20	
VDRM	Repetitive peak off-state voltage *1	1000	V
VDSM	Non-repetitive peak off-state voltage *1	1200	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, Tc=88°C	8	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	80	A
I ² t	I ² t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	26	A ² s
P _{GM}	Peak gate power dissipation		5	W
P _{G (AV)}	Average gate power dissipation		0.5	W
V _{GM}	Peak gate voltage		10	V
I _{GM}	Peak gate current		2	A
T _J	Junction temperature		-40 ~ +125	°C
T _{stg}	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	2.0	g
Viso	Isolation voltage	Ta=25°C, AC 1 minute, T1 · T2 · G terminal to case	2000	V

*1. Gate open.

Mar. 2002

BCR8PM-20

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ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
IDRM	Repetitive peak off-state current	T _J =125°C, V _{DRM} applied	—	—	2.0	mA	
V _{TM}	On-state voltage	T _c =25°C, I _{TM} =12A, Instantaneous measurement	—	—	1.6	V	
V _{FGT I}	Gate trigger voltage *2	T _J =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	I	—	—	1.5	V
V _{RGT I}			II	—	—	1.5	V
V _{RGT III}			III	—	—	1.5	V
I _{FGT I}	Gate trigger current *2	T _J =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	I	—	—	30	mA
I _{RGT I}			II	—	—	30	mA
I _{RGT III}			III	—	—	30	mA
V _{GD}	Gate non-trigger voltage	T _J =125°C, V _D =1/2V _{DRM}	0.2	—	—	V	
R _{th (j-c)}	Thermal resistance	Junction to case *3	—	—	3.7	°C/W	
(dv/dt) _c	Critical-rate of rise of off-state commutating voltage *4	T _J =125°C	10	—	—	V/μs	

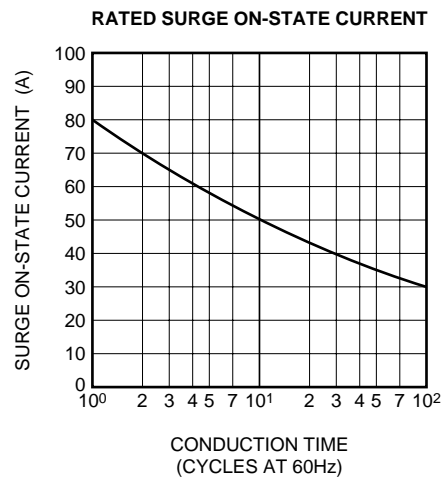
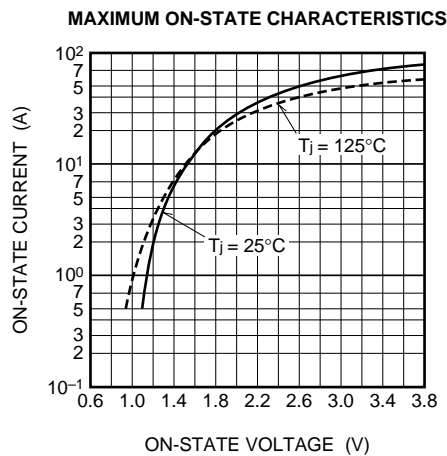
*2. Measurement using the gate trigger characteristics measurement circuit.

*3. The contact thermal resistance R_{th (c-f)} in case of greasing is 0.5°C/W.

*4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature T _J =125°C 2. Rate of decay of on-state commutating current (di/dt) _c =-4.0A/ms 3. Peak off-state voltage V _D =400V	

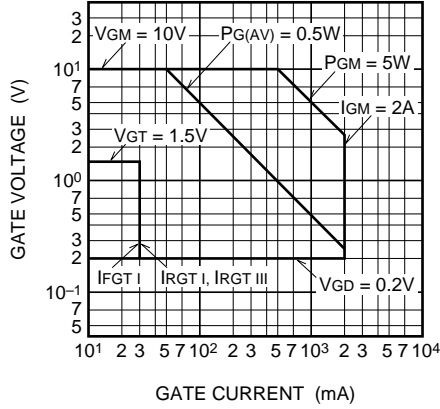
PERFORMANCE CURVES



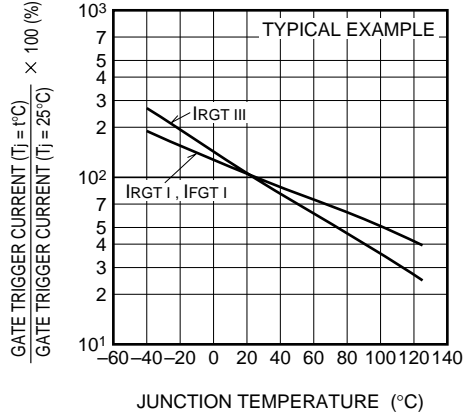
BCR8PM-20

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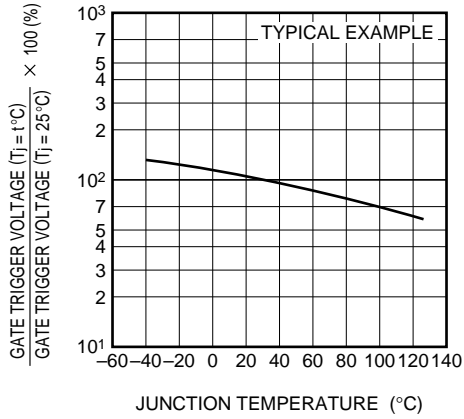
GATE CHARACTERISTICS



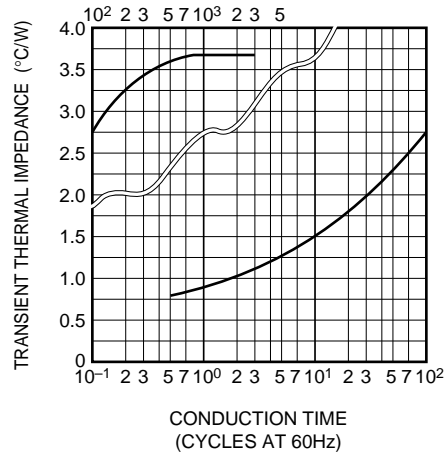
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



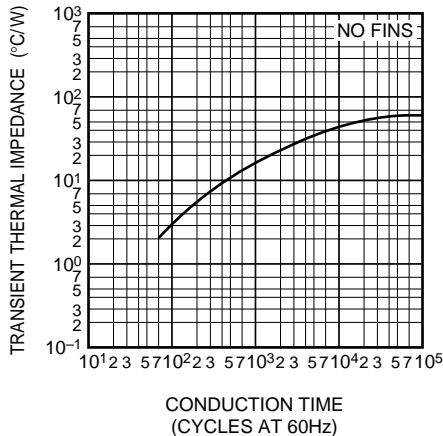
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



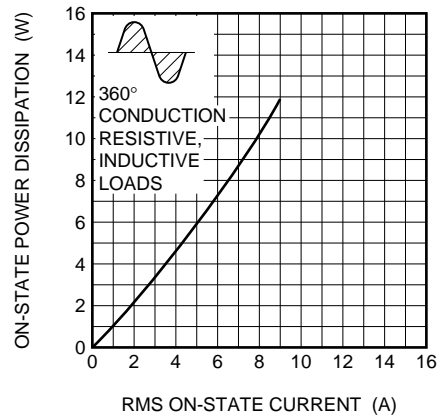
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)



MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO AMBIENT)

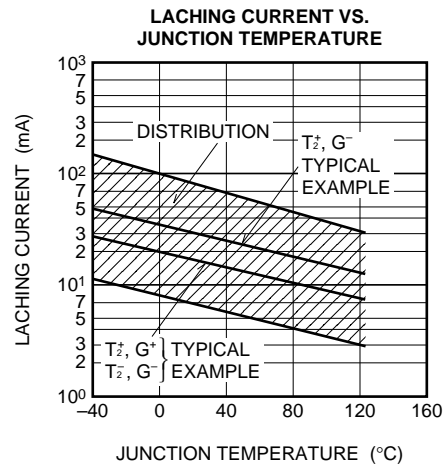
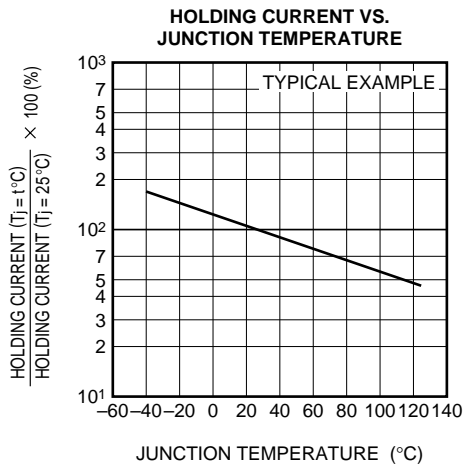
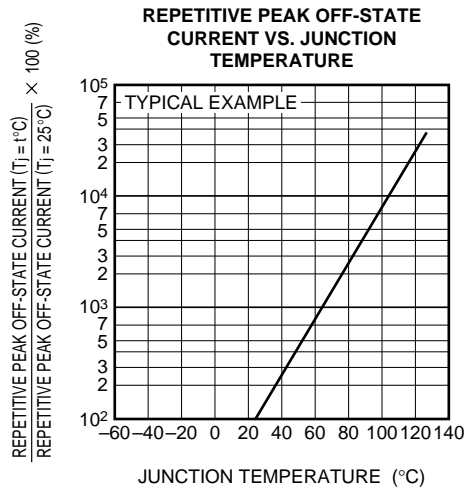
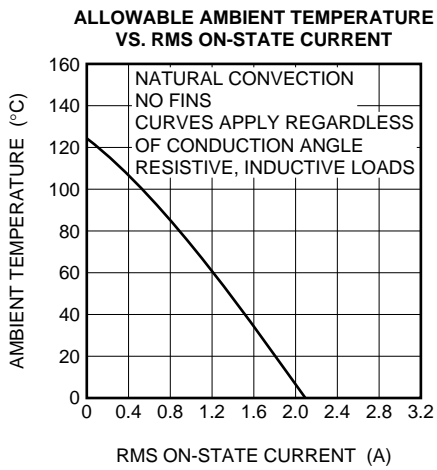
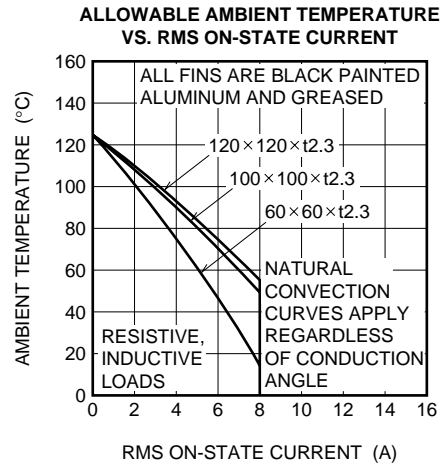
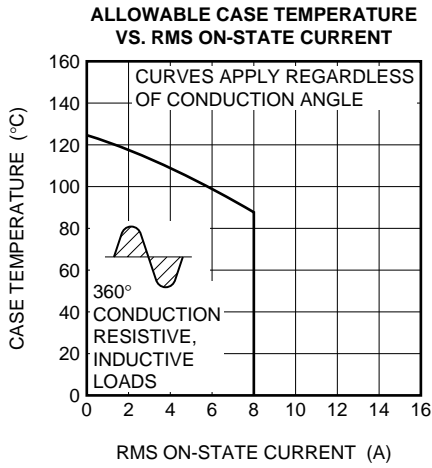


MAXIMUM ON-STATE POWER DISSIPATION



BCR8PM-20

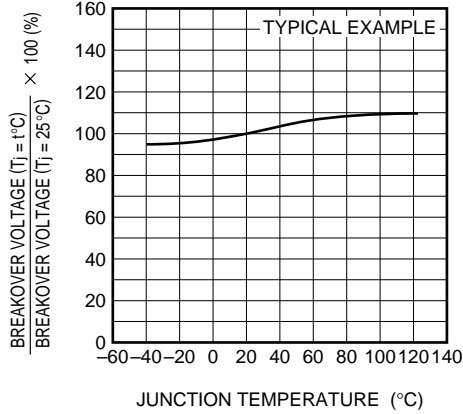
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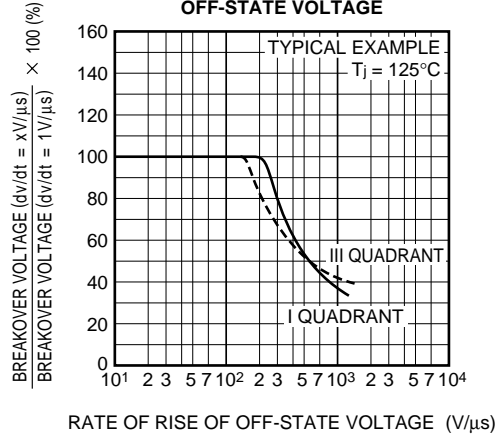
BCR8PM-20

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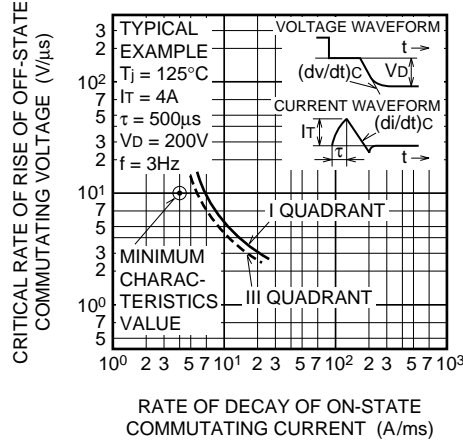
BREAKEOVER VOLTAGE VS. JUNCTION TEMPERATURE



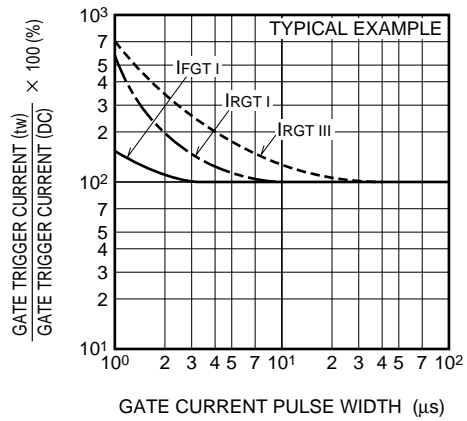
BREAKEOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE



COMMUTATION CHARACTERISTICS



GATE TRIGGER CURRENT VS. GATE CURRENT PULSE WIDTH



GATE TRIGGER CHARACTERISTICS TEST CIRCUITS

